■ Flash Memories

Capacity	Configuration (words x bits)	Erasable block size (bytes)	Model No.	Access time (ns) MAX.	Supply voltage (V)	Read current (mA)MAX.	Operating temperature (℃)	Package
2M	256k x 8	16k	★LH28F020SUT/N-N60	60	Vcc=5 Vpp=5	50	0 to 70	32TSOP(I) Forward bend/ 32SOP
			★LH28F020SUT/N-N80	80				
			★LH28F020SUT/N-L12	120	Vcc=3.3 Vpp=5	30		
			★LH28F020SUT/N-L15	150				
4M	512k x 8	64k/32k/16k (Fixed at factory)	★LH28F004SUT-N60	60	Vcc=5 Vpp=5	55	0 to 70	40TSOP(I) Forward bend
			LH28F004SUT-N80	80				
			LH28F004SUT-L12	120	Vcc=3.3 Vpp=5	35		
			LH28F004SUT-L15	150				
		16k	★LH28F004SUHT-N80	80	Vcc=5 Vpp=5	55	− 40 to 85	
			★LH28F004SUHT-L12	120	Vcc=3.3 Vpp=5	35		
			★LH28F004SUHT-L15	150				
	512k x 8 256k x 16	64k/32k/16k (Fixed at factory)	★LH28F400SUT/N-N60	60	Vcc=5 Vpp=5	55	0 to 70	56TSOP(I) Forward bend/ 44SOP
			LH28F400SUT/N-N80	80				
			LH28F400SUT/N-L12	120	Vcc=3.3 Vpp=5	35		
			LH28F400SUT/N-L15	150				
		16k	★LH28F400SUHT/N-N80	80	Vcc=5 Vpp=5	55	− 40 to 85	
			★LH28F400SUHT/N-L12	120	Vcc=3.3 Vpp=5	35		
			★LH28F400SUHT/N-L15	150				
8M	1M x 8	64k	LH28F008SAT/R/N-85	85	Vcc=5 Vpp=12	50	0 to 70	40TSOP(I)/44SOP
			LH28F008SAT/R/N-12	120				
			★LH28F008SAHT/R/N-85	85		TBD	− 40 to 85	
			★LH28F008SAHT/R/N-12	120				
	1M x 8 512k x 16	64k	LH28F800SUT/R-70	70*1/120*2	Vcc=5/3.3 Vpp=5	60*1/35*2	0 to 70	56TSOP(I)
			LH28F800SUT/R-10	100*1/150*2				
			★LH28F800SUHT/R-70	70*1/120*2			− 40 to 85	
			★LH28F800SUHT/R-10	100*1/150*2				
16M	2M x 8 1M x 16	64k	LH28F016SAT/R-70	70*1/120*2	Vcc=5/3.3 Vpp=12	60*1/35*2	0 to 70	56TSOP(I)
			LH28F016SAT/R-10	100*1/150*2				
			LH28F016SUT/R-70	70*1/120*2	Vcc=5/3.3 Vpp=5			
			LH28F016SUT/R-10	100*1/150*2				
			★LH28F016SUHT/R-70	70*1/120*2			− 40 to 85	
			★LH28F016SUHT/R-10	100*1/150*2				
32M	4M x 8 2M x 16	64k	LH28F032SUTD-70	70*1/120*2	Vcc=5/3.3 Vpp=5	60*1/35*2	0 to 70	56TSOP(I) Forward bend
			LH28F032SUTD-10	100*1/150*2				

*1 Vcc = 5 V *2 Vcc = 3.3 V